

## TO-92MOD Plastic-Encapsulated Transistors

### 2SB892 TRANSISTOR (PNP)

#### FEATURE

Power dissipation

$$P_{CM}: 1 \text{ W (Tamb=25°C)}$$

Collector current

$$I_{CM}: -2 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -60 \text{ V}$$

Operating and storage junction temperature range

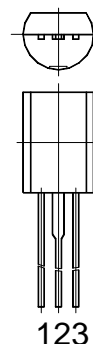
$$T_J, T_{stg}: -55°C \text{ to } +150°C$$

#### TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-6		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$		-0.1	$\mu A$
DC current gain	$H_{FE(1)}$	$V_{CE} = -2V, I_C = -100mA$	100	560	
	$H_{FE(2)}$	$V_{CE} = -2V, I_C = -1.5A$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -50mA$		-1.2	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -50mA$	150		MHz

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560